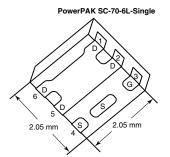
SQA410EJ



Vishay Siliconix

Automotive N-Channel 20 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	20			
$R_{DS(on)} (\Omega)$ at $V_{GS} = 4.5 V$	0.028			
$R_{DS(on)}$ (Ω) at V_{GS} = 2.5 V	0.034			
$R_{DS(on)} (\Omega)$ at $V_{GS} = 1.8 V$	0.038			
I _D (A)	7.8			
Configuration	Single			



Ordering Information: SQA410EJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

Halogen-free According to IEC 61249-2-21
Definition

Lot Traceability and Date code

• TrenchFET[®] Power MOSFET

Marking Code

XXX

- AEC-Q101 Qualified ^d
- 100 % $\rm R_g$ and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



N-Channel MOSFET

ORDERING INFORMATION			
Package	PowerPAK SC-70		
Lead (Pb)-free and Halogen-free	SQA410EJ-T1-GE3		

Part # code

ABSOLUTE MAXIMUM RATINGS ($T_C = 25 \text{ °C}$, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	20	V	
Gate-Source Voltage		V _{GS} ± 8		V	
Continuous Drain Current ^a	T _C = 25 °C	I-	7.8		
	T _C = 125 °C	I _D	7.8		
Continuous Source Current (Diode Conduction) ^a		I _S	7.8	А	
Pulsed Drain Current ^a			24		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	10		
Single Pulse Avalanche Energy	L = 0.1 IIIA	E _{AS}	5	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	P _D	13.6	W	
	T _C = 125 °C		4.5	vv	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 175	°C	
Soldering Recommendations (Peak Temperature) ^{e, f}			260	C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	90	°C/W	
Junction-to-Case (Drain)		R _{thJC}	11		

Notes

a. Package limited.

b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

c. When mounted on 1" square PCB (FR-4 material).

d. Parametric verification ongoing.

e. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static		•				•		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = 250 \mu\text{A}$		20	-	-	v	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$		0.6	1.1		
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 8 V$		-	-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 20 V	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 20 V, T _J = 125 °C	-	-	50	μA	
		$V_{GS} = 0 V$	$V_{DS} = 20 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	250		
On-State Drain Current ^a	I _{D(on)}	$V_{GS} = 4.5 V$	$V_{DS} \ge 5 V$	10	-	-	Α	
		$V_{GS} = 4.5 V$	I _D = 5 A	-	0.023	0.028	Ω	
		$V_{GS} = 4.5 V$	I _D = 5 A, T _J = 125 °C	-	-	0.042		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 V$	I _D = 5 A, T _J = 175 °C	-	-	0.050		
		$V_{GS} = 2.5 V$	$I_D = 4 A$	-	0.026	0.034		
		V _{GS} = 1.8 V	I _D = 3 A	-	0.031	0.038		
Forward Transconductanceb	9 _{fs}	V _{DS}	= 15 V, I _D = 5 A	-	31	-	S	
Dynamic ^b	•	·					•	
Input Capacitance	C _{iss}		_S = 0 V V _{DS} = 10 V, f = 1 MHz	-	388	485	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$		-	80	100		
Reverse Transfer Capacitance	C _{rss}			-	36	45		
Total Gate Charge ^c	Qg			-	5	8		
Gate-Source Charge ^c	Q _{gs}	$V_{GS} = 4.5 V$	V V _{DS} = 10 V, I _D = 5.1 A	-	0.55	-	nC	
Gate-Drain Charge ^c	Q _{gd}			-	0.79	-		
Gate Resistance	R _g	f = 1 MHz		6	11.89	18	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	8	12		
Rise Time ^c	t _r	$\label{eq:VDD} \begin{array}{l} V_{\text{DD}} = 10 \; V, R_{\text{L}} = 10 \; \Omega \\ I_{\text{D}} \cong 1 \; A, V_{\text{GEN}} = 4.5 \; V, R_{\text{g}} = 1 \; \Omega \end{array}$		-	8	12	ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	21	32		
Fall Time ^c	t _f			-	8	12		
Source-Drain Diode Ratings and Char	acteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	24	Α	
Forward Voltage	V _{SD}	$I_{\rm F} = 4.5 \text{ A}, V_{\rm GS} = 0 \text{ V}$		-	0.75	1.2	V	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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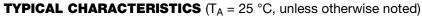
On-Resistance vs. Drain Current

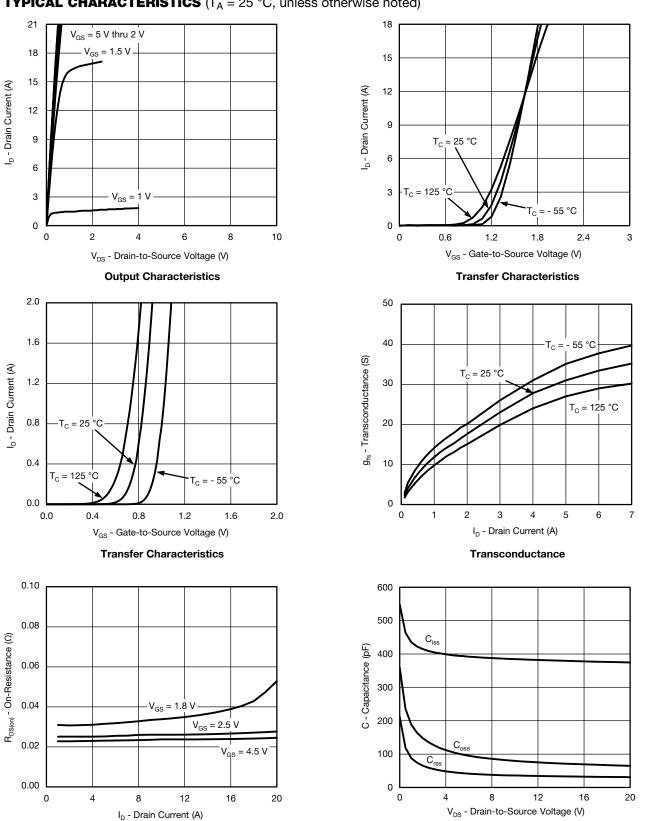
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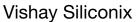
Capacitance

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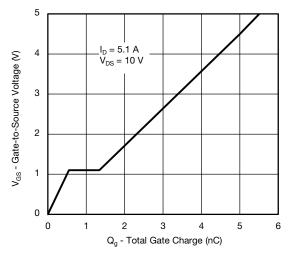
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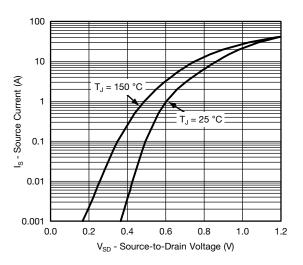
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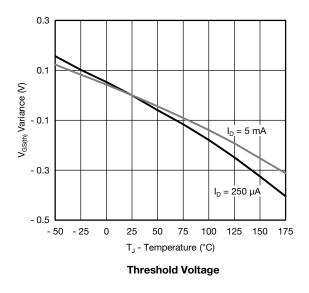
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)

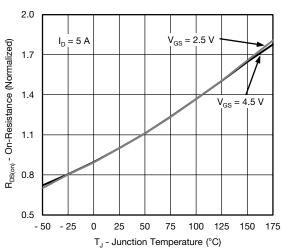




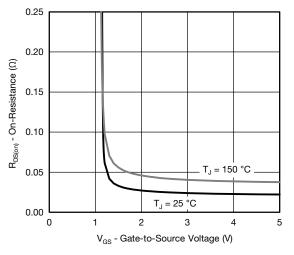


Source Drain Diode Forward Voltage

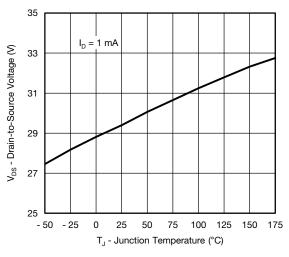




On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature

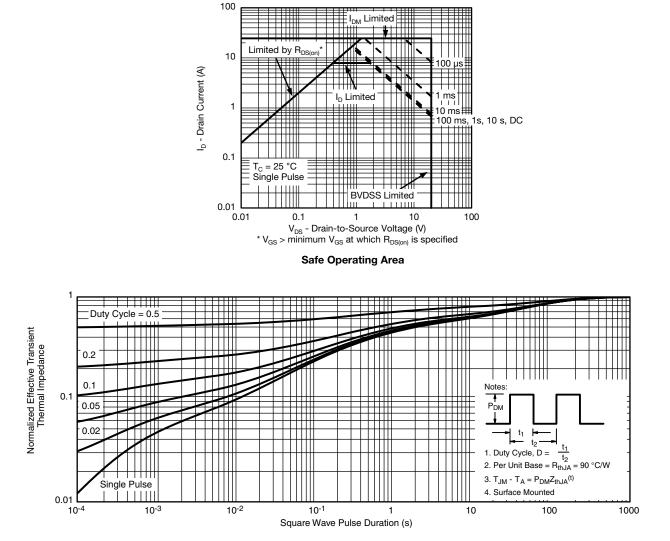
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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

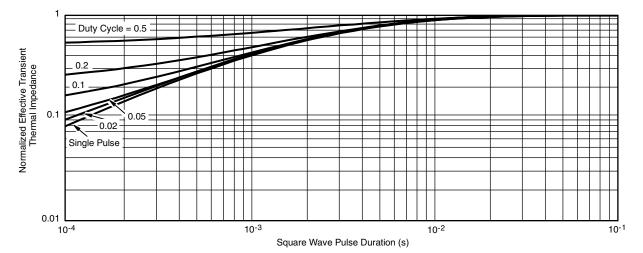
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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?67072.



Vishay Siliconix

PowerPAK[®] SC-70

Ordering codes for the SQ rugged series power MOSFETs in the PowerPAK SC-70 package:

DATASHEET PART NUMBER	OLD ORDERING CODE ^a	NEW ORDERING CODE
SQA410EJ	SQA410EJ-T1-GE3	SQA410EJ-T1_GE3

Note

a. Old ordering code is obsolete and no longer valid for new orders



PowerPAK[®] SC70-6L

VISHA

b PIN2 PIN1 PIN3 _ ₹



b

PIN3

__ ₿

PIN2

PIN1

¥

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¹



RECOMMENDED PAD LAYOUT FOR PowerPAK[®] SC70-6L Single



Dimensions in mm/(Inches)

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